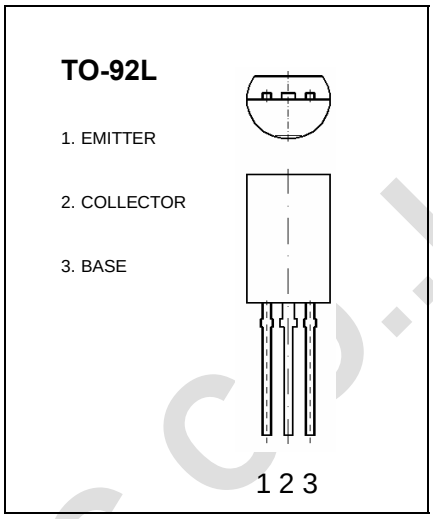
KTC3227 TRANSISTOR (NPN)



FEATURES

Power dissipation

P_{CM}: 1 W (Tamb=25℃)

Collector current

I_{CM}: 400 mA

Collector-base voltage

$V_{(BR)CBO}$: 80 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= 1mA, I_E=0	80			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= 5 mA , I_B=0	80			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 1 mA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=50V, I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V, I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}= 2V, I_C= 50mA	70		240	
	$h_{FE(2)}$	V_{CE}= 2V, I_C= 200mA	40			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C= 200mA, I_B= 20mA			0.4	V
Base-emitter voltage	V_{BE}	V_{CE}= 2V, I_C= 5mA	0.55		0.8	V
Transition frequency	f_T	V_{CE}= 10V, I_C= 10mA		80		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz		10		pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	70-140	120-240